

2MBI600XHA120-50

IGBT Modules

Power Module (X series)
1200V / 600A / 2-in-1 package

■ **Features**

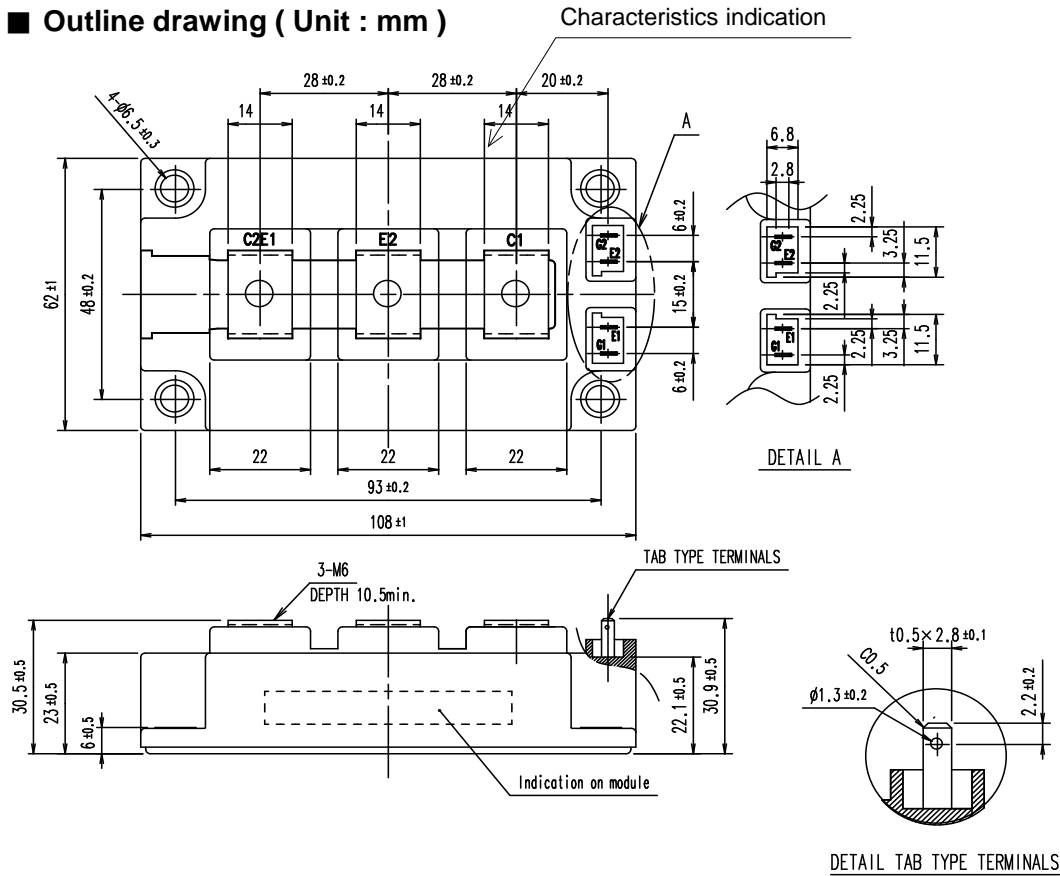
- Low $V_{CE(sat)}$
- High speed switching
- Low Inductance Module structure

■ **Applications**

- Inverter for Motor Drives, AC and DC Servo Drives
- Uninterruptible Power Supply Systems,
- Industrial machines, such as Welding machines

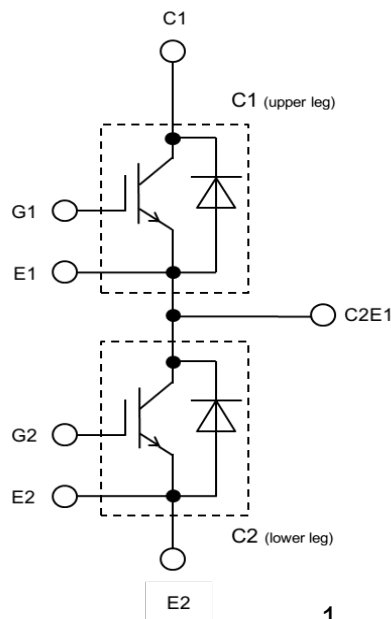


■ **Outline drawing (Unit : mm)**



Weight: 370 g(typ.)

■ **Equivalent Circuit**



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■ Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units
Inverter	Collector-Emitter voltage Gate-Emitter short-circuited	V_{CES}		1200	V
	Gate-Emitter voltage Collector-Emitter short-circuited	V_{GES}		± 20	V
	Collector current	I_C	Continuous $T_c=100^\circ\text{C}$	600	A
	Repetitive peak collector current	I_{CRM}	1ms	1200	
	Forward current	I_F		600	
	Repetitive peak forward current	I_{FRM}	1ms	1200	
	Total power dissipation	P_{tot}	1 device	2340	W
	Virtual junction temperature	T_{vj}		175	°C
	Operating virtual junction temperature	T_{vjop}		175	
	Case temperature	T_c		125	
Storage temperature	T_{stg}		-40 ~ 125		
Isolation voltage	between terminal and copper base (*1)	V_{isol}	AC: 1min.	4000	Vrms
Mounting torque of screws to heat sink (*2)		M_s	M5 or M6	6.0	N·m
Mounting torque of screws to terminals (*2)		M_t	M6	5.0	

(*1) All terminals should be connected together during the test.

(*2) Recommendable Value: Mounting 3.0 ~ 6.0 N·m (M5 or M6)
 Terminals 2.5 ~ 5.0 N·m (M6)

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■ Electrical characteristics (at $T_{vj}= 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	-	-	200	μA	
Gate leakage current, Collector-Emitter short-circuited	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-	-	400	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 600\text{mA}$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 600\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.70	2.15	V
	$V_{CE(sat)}$ (chip)		$T_{vj}=25^{\circ}\text{C}$	-	1.45	1.90	
			$T_{vj}=125^{\circ}\text{C}$	-	1.85	-	
			$T_{vj}=150^{\circ}\text{C}$	-	1.90	-	
Internal Gate resistance	r_g	-	-	1.63	-	Ω	
	Capacitance	C_{ies}	$V_{CE}=10\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	-	63	-	nF
		C_{oes}		-	2.1	-	
		Cr_{es}		-	0.56	-	
Gate charge	Q_G	$V_{CC} = 600\text{V}, I_C = 600\text{A}$ $V_{GE} = -15 \rightarrow +15\text{V}$	-	4.0	-	μC	
Forward on voltage	V_F (terminal)	$V_{GE} = 0\text{V}$ $I_F = 600\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.90	2.35	V
	V_F (chip)		$T_{vj}=25^{\circ}\text{C}$	-	1.65	2.10	
			$T_{vj}=125^{\circ}\text{C}$	-	1.70	-	
			$T_{vj}=150^{\circ}\text{C}$	-	1.65	-	
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600\text{V}$ $I_C, I_F = 600\text{A}$ $V_{GE} = +15/-15\text{V}$ $R_G = 0.56 \Omega$ $L_S = 30 \text{ nH}$	$T_{vj}=25^{\circ}\text{C}$	-	0.30	-	μs
			$T_{vj}=125^{\circ}\text{C}$	-	0.33	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.34	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.35	-	
	t_r		$T_{vj}=25^{\circ}\text{C}$	-	0.07	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.08	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.08	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.09	-	
	$t_{d(off)}$		$T_{vj}=25^{\circ}\text{C}$	-	0.39	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.43	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.45	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.45	-	
t_f	$T_{vj}=25^{\circ}\text{C}$	-	0.12	-			
	$T_{vj}=125^{\circ}\text{C}$	-	0.16	-			
	$T_{vj}=150^{\circ}\text{C}$	-	0.17	-			
	$T_{vj}=175^{\circ}\text{C}$	-	0.18	-			
Reverse recovery time	t_{rr}	$T_{vj}=25^{\circ}\text{C}$	-	0.15	-		
		$T_{vj}=125^{\circ}\text{C}$	-	0.26	-		
		$T_{vj}=150^{\circ}\text{C}$	-	0.28	-		
		$T_{vj}=175^{\circ}\text{C}$	-	0.31	-		

 (*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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■ Electrical characteristics (at $T_{vj}= 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Inverter Switching loss (per pulse)	E_{on}	$V_{CC} = 600\text{V}$ $I_C, I_F = 600\text{A}$ $V_{GE} = +15/ -15\text{V}$ $R_G = 0.56 \Omega$ $L_S = 30 \text{ nH}$	$T_{vj}=25^{\circ}\text{C}$	-	13.6	-	mJ
			$T_{vj}=125^{\circ}\text{C}$	-	23.1	-	
			$T_{vj}=150^{\circ}\text{C}$	-	25.4	-	
			$T_{vj}=175^{\circ}\text{C}$	-	27.8	-	
	E_{off}		$T_{vj}=25^{\circ}\text{C}$	-	58.2	-	
			$T_{vj}=125^{\circ}\text{C}$	-	68.4	-	
			$T_{vj}=150^{\circ}\text{C}$	-	71.0	-	
			$T_{vj}=175^{\circ}\text{C}$	-	73.6	-	
	E_{rr}		$T_{vj}=25^{\circ}\text{C}$	-	30.1	-	
			$T_{vj}=125^{\circ}\text{C}$	-	46.0	-	
			$T_{vj}=150^{\circ}\text{C}$	-	50.0	-	
			$T_{vj}=175^{\circ}\text{C}$	-	54.0	-	

NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

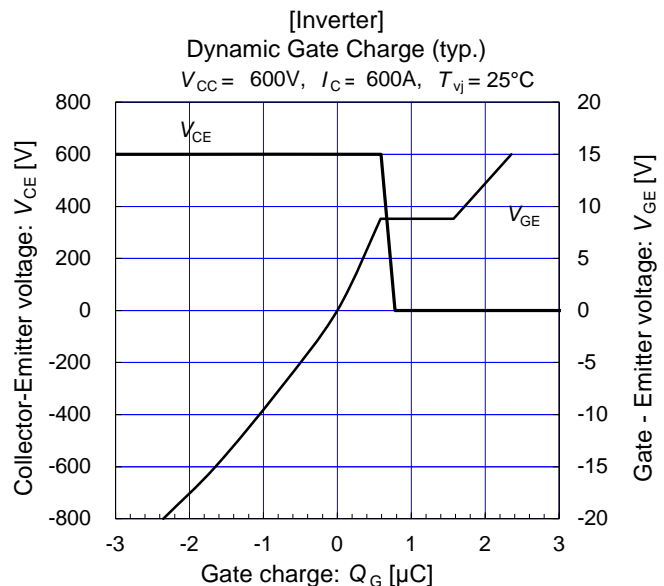
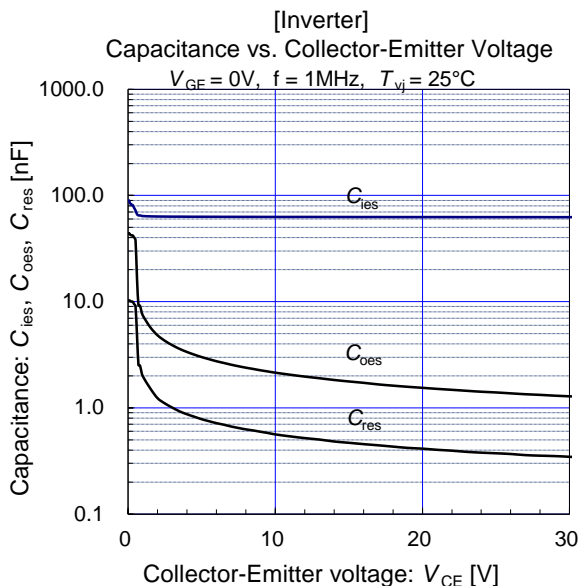
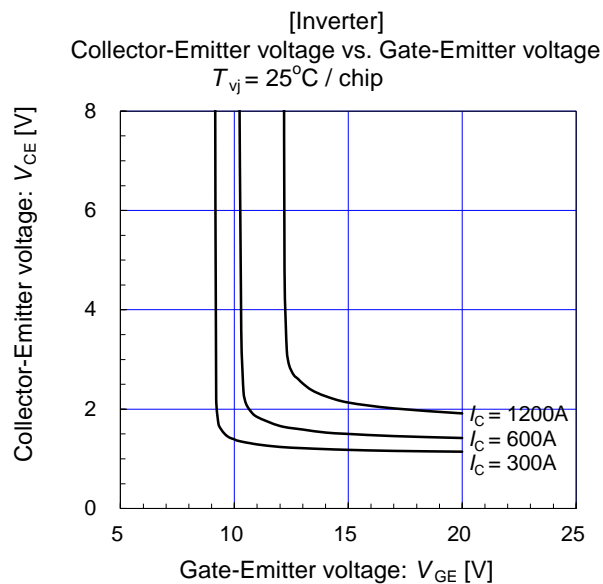
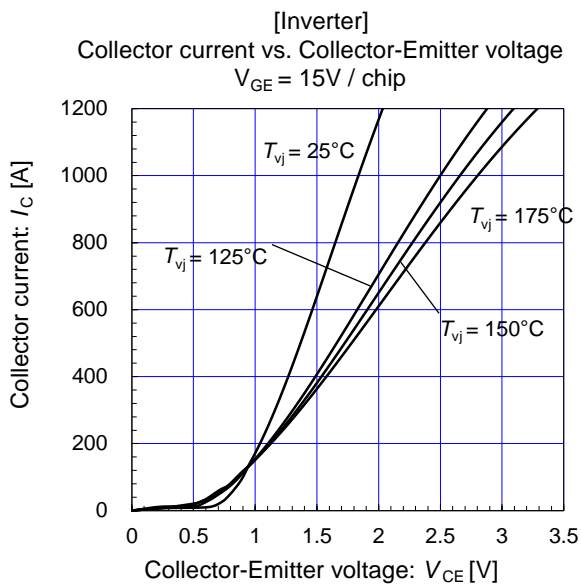
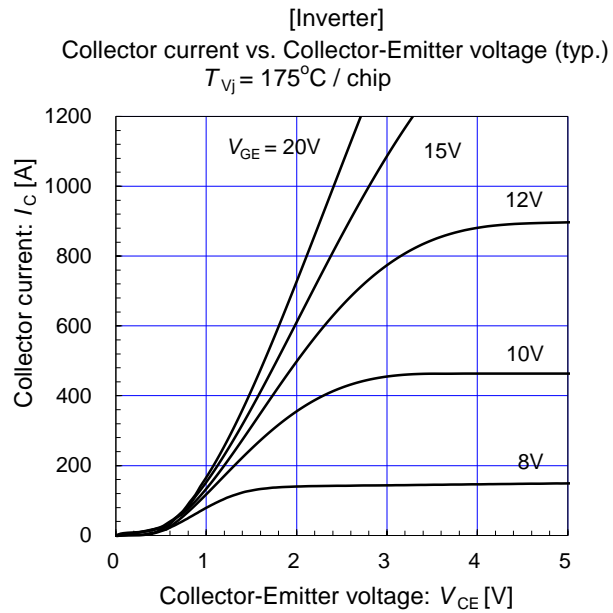
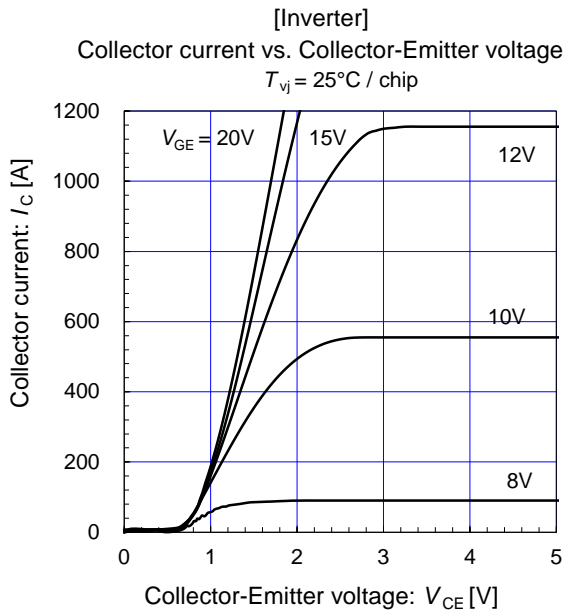
■ Thermal resistance characteristics

	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance junction to case (1 device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.064	$^{\circ}\text{C/W}$
		Inverter FWD	-	-	0.090	
Thermal resistance case to heat sink (1IGBT + 1FWD) (*1)	$R_{th(c-s)}$	with 1 W/(m·K) thermal grease	-	0.0125	-	

(*1) This is the value which is defined mounting on the additional cooling fin with thermal compound.

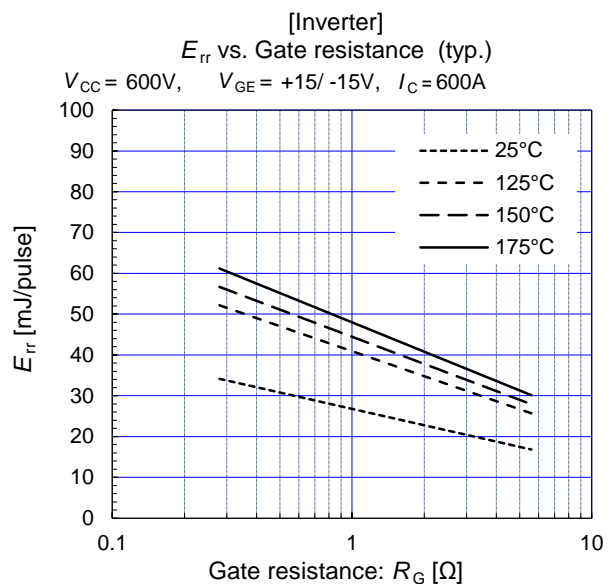
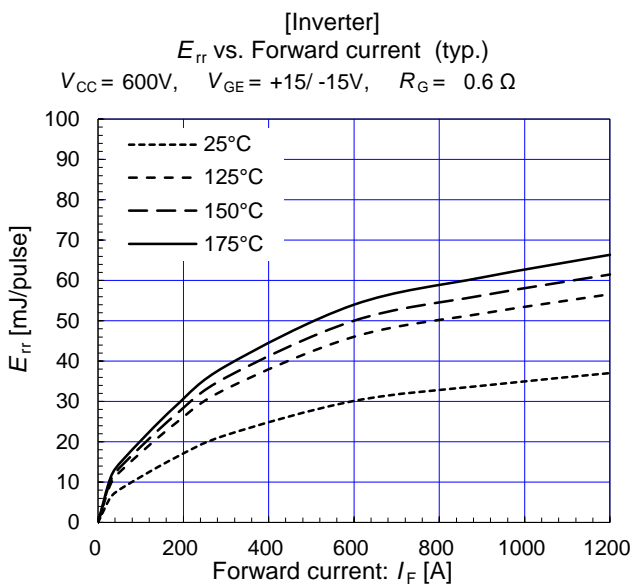
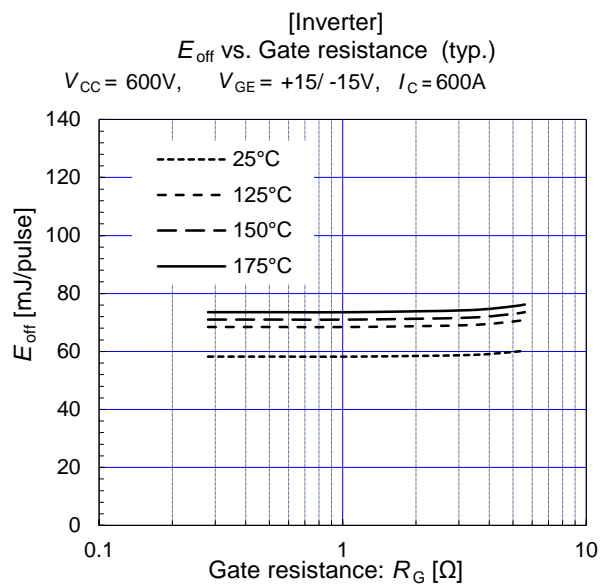
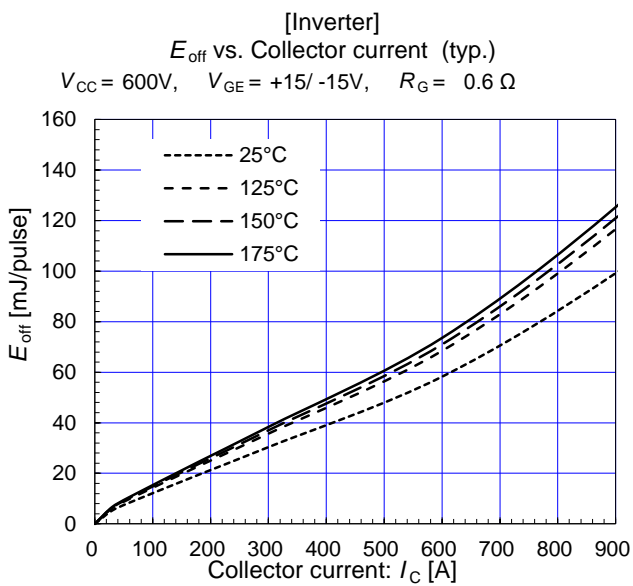
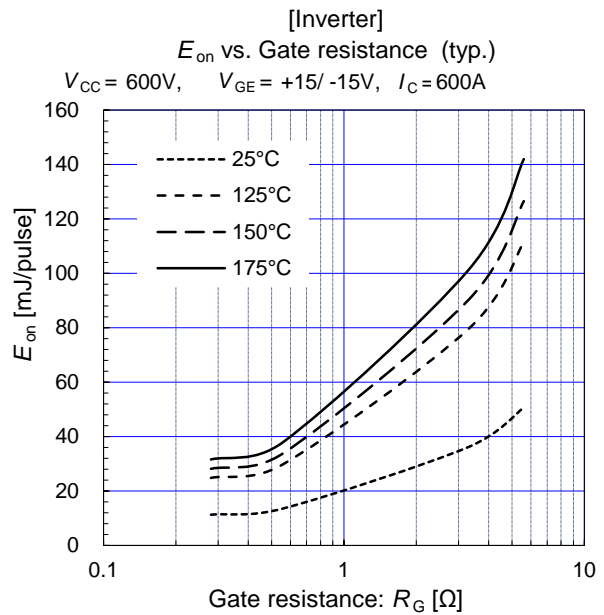
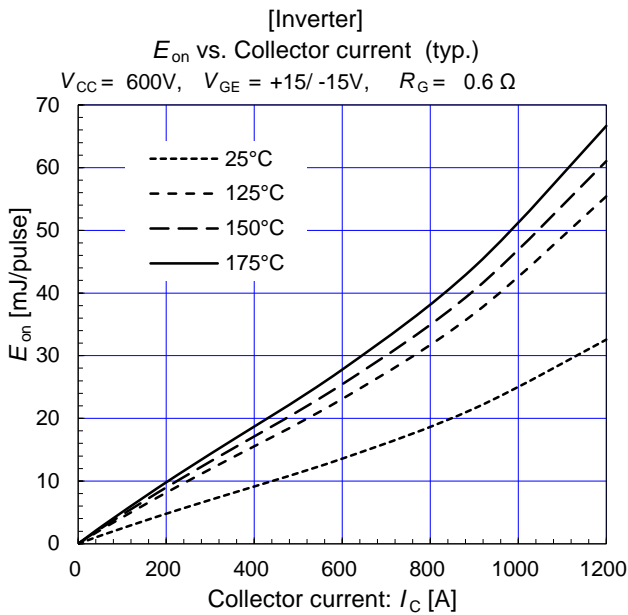
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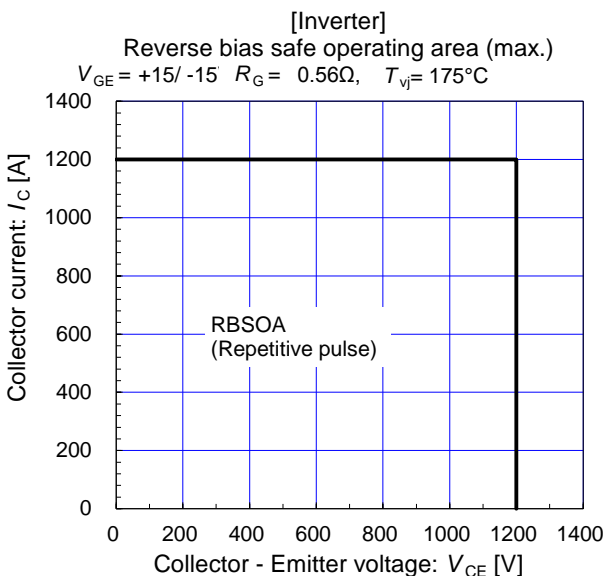
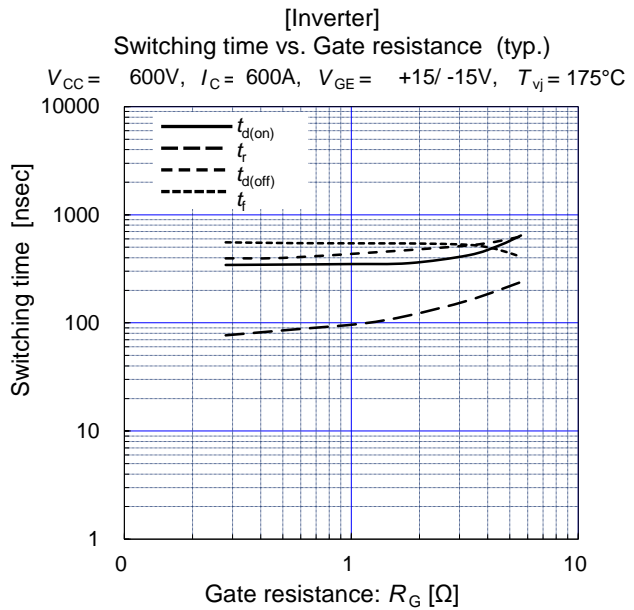
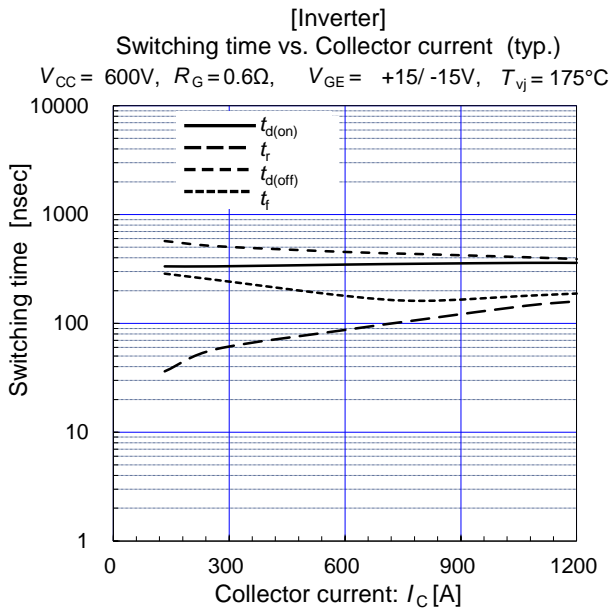
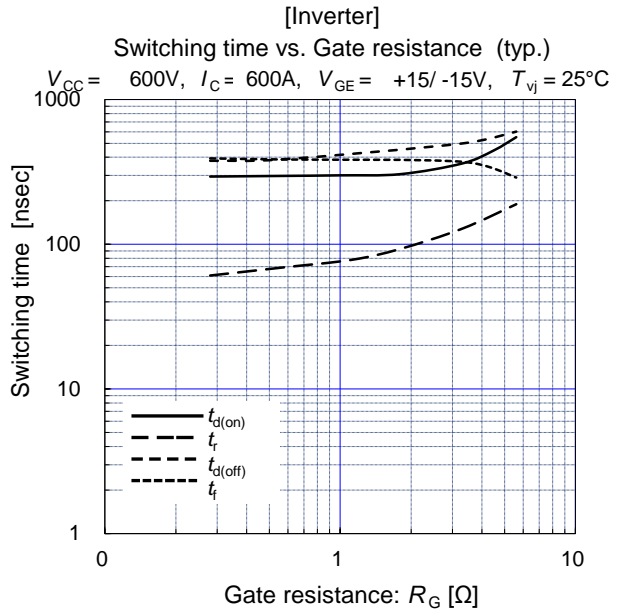
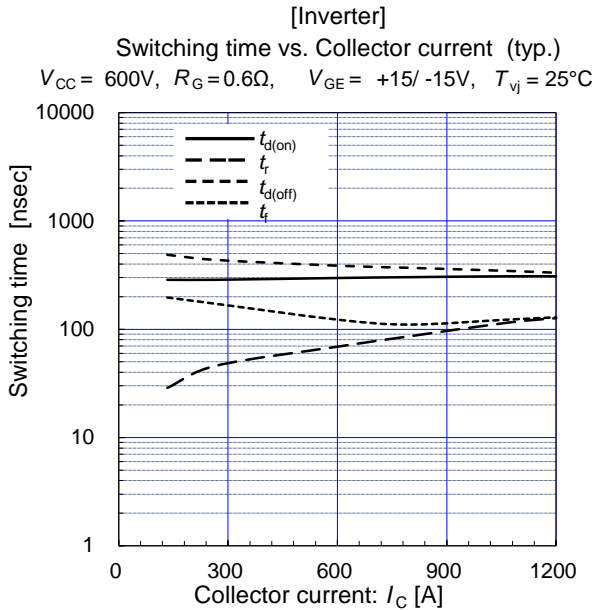
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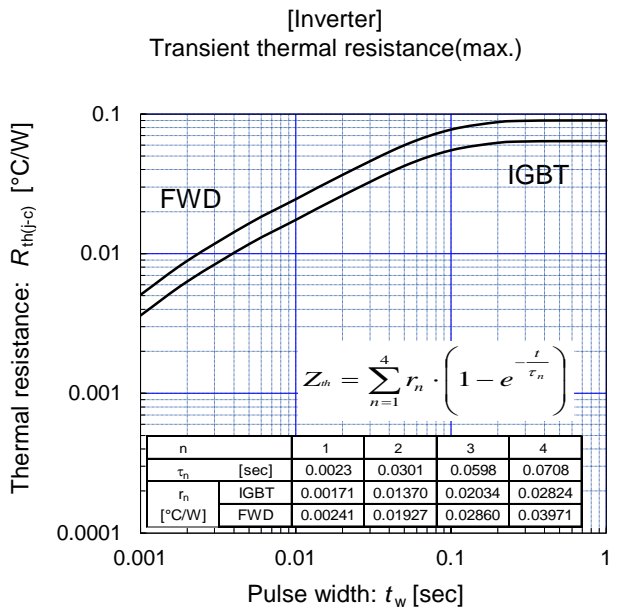
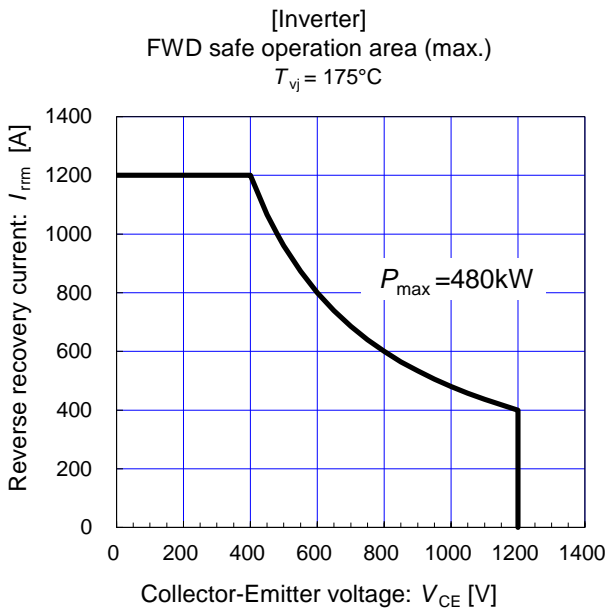
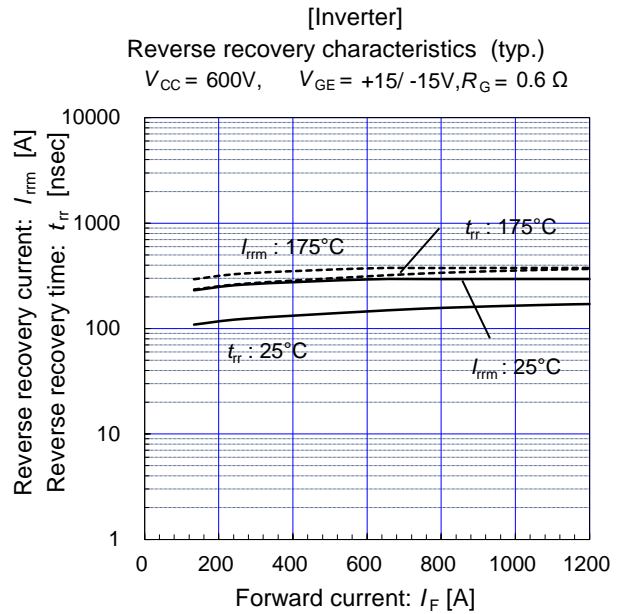
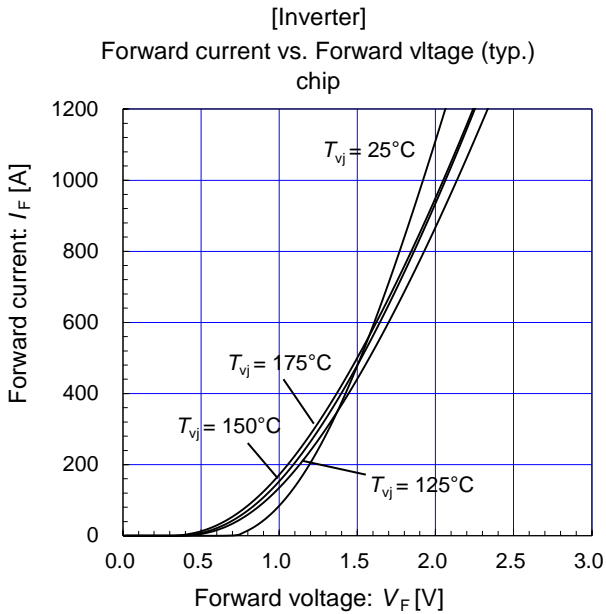
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